

HIGH VOLTAGE APPLICATION.

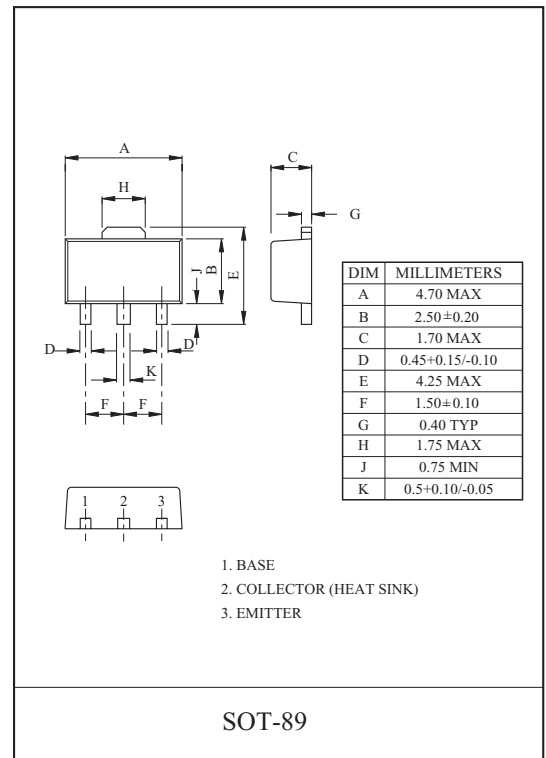
### FEATURES

- High Breakdown Voltage.

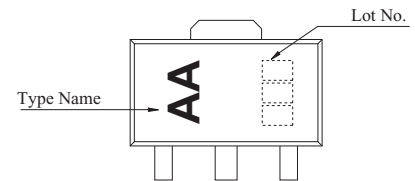
### MAXIMUM RATING (Ta=25 )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-400	V
Collector-Emitter Voltage	$V_{CEO}$	-400	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Collector Current	$I_C$	-100	mA
Collector Power Dissipation	$P_C$	500	mW
	$P_C^*$	1	W
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

$P_C^*$  : Mounted on Ceramic Substrate (250mm<sup>2</sup> × 0.85)



### Marking



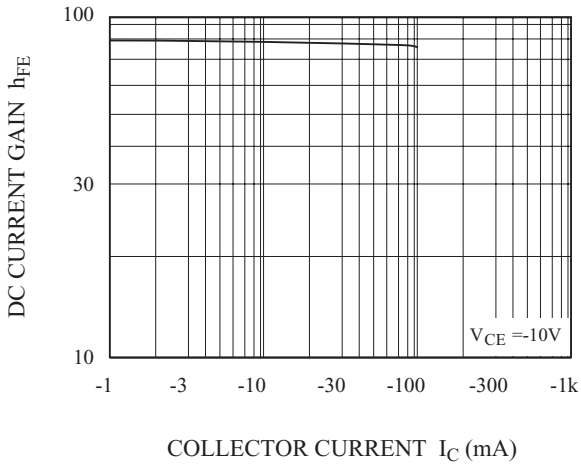
### ELECTRICAL CHARACTERISTICS (Ta=25 )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -50 \mu A, I_E = 0$	-400	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-400	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -50 \mu A, I_C = 0$	-7.0	-	-	V
Collector Cut off Current	$I_{CBO}$	$V_{CB} = -400V, I_E = 0$	-	-	-10	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = -6V, I_C = 0$	-	-	-10	$\mu A$
DC Current Gain *	$h_{FE}$	$V_{CE} = -10V, I_C = -10mA$	50	-	300	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)}$ <sup>2</sup>	$I_C = -20mA, I_B = -2mA$	-	-	-0.5	V
Base-Emitter Saturation Voltage *	$V_{BE(sat)}$	$I_C = -20mA, I_B = -2mA$	-	-	-1.5	V

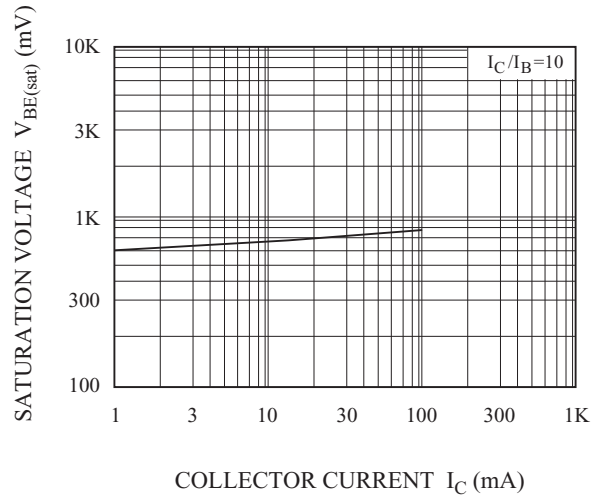
\*Pulse Test : Pulse Width 300  $\mu s$ , Duty Cycle 2%

# KTA1759

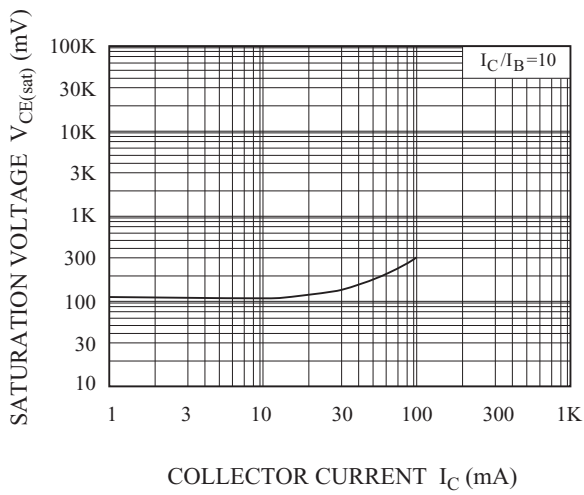
$h_{FE} - I_C$



$V_{BE(sat)} - I_C$



$V_{CE(sat)} - I_C$



$C_{ob} - V_{CB}$

